Complementary Silicon Plastic Power Transistors

Designed for use in general purpose amplifier and switching applications.

Features

- High Current Gain Bandwidth Product
- Compact TO-220 AB Package
- Epoxy Meets UL94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	BD242B	BD241C BD242C	Unit
Collector–Emitter Voltage	V_{CEO}	80	100	Vdc
Collector–Emitter Voltage	V _{CES}	90	115	Vdc
Emitter-Base Voltage	V _{EB}	5.	.0	Vdc
Collector Current -Continuous	I _C	3.0		Adc
Collector Current - Peak	I _{CM}	5.0		Adc
Base Current	I _B	1.0		Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	40 0.32		W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150		°C
ESD – Human Body Model	НВМ	3B		V
ESD – Machine Model	MM	(V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	°C/W



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POWER TRANSISTORS
COMPLEMENTARY
SILICON
3 AMP
80-100 VOLTS
40 WATTS

COMPLEMENTARY

COLLECTOR 2,4

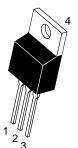
1
BASE

EMITTER 3

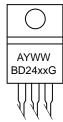
COLLECTOR 2,4

BASE

EMITTER 3



MARKING DIAGRAM



BD24xx = Device Code

TO-220 CASE 221A

STYLE 1

xx = 1C, 2B, or 2C

A = Assembly Location Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
BD241CG	TO-220 (Pb-Free)	50 Units/Rail
BD242BG	TO-220 (Pb-Free)	50 Units/Rail
BD242CG	TO-220 (Pb-Free)	50 Units/Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit				
OFF CHARACTERISTICS								
Collector–Emitter Sustaining Voltage (Note 1) $(I_C = 30 \text{ mAdc}, I_B = 0)$	BD242B BD241C, BD242C	V _{CEO}	80 100		Vdc			
Collector Cutoff Current ($V_{CE} = 50 \text{ Vdc}, I_B = 0$) ($V_{CE} = 60 \text{ Vdc}, I_B = 0$)	BD242B BD241C, BD242C	I _{CEO}		0.3	mAdc			
Collector Cutoff Current ($V_{CE} = 80 \text{ Vdc}, V_{EB} = 0$) ($V_{CE} = 100 \text{ Vdc}, V_{EB} = 0$)	BD242B BD241C, BD242C	I _{CES}		200	μAdc			
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0$)		I _{EBO}		1.0	mAdc			
ON CHARACTERISTICS (Note 1)								
DC Current Gain ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 4.0 \text{ Vdc}$) ($I_C = 3.0 \text{ Adc}$, $V_{CE} = 4.0 \text{ Vdc}$)		h _{FE}	25 10					
Collector–Emitter Saturation Voltage (I _C = 3.0 Adc, I _B = 0.6 Adc)		V _{CE(sat)}		1.2	Vdc			
Base–Emitter On Voltage (I _C = 3.0 Adc, V _{CE} = 4.0 Vdc)		V _{BE(on)}		1.8	Vdc			
DYNAMIC CHARACTERISTICS								
Current Gain – Bandwidth Product (Note 2) (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 1.0 MHz)		f _T	3.0		MHz			
Small–Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{fe}	20					

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

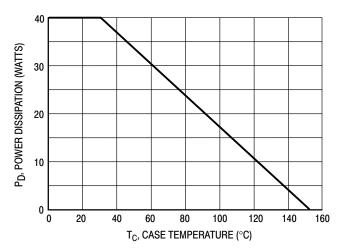


Figure 1. Power Derating

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

^{2.} $f_T = |h_{fe}| \bullet f_{test}$.

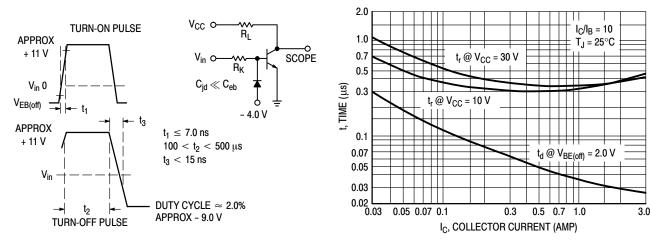


Figure 2. Switching Time Equivalent Circuit

Figure 3. Turn-On Time

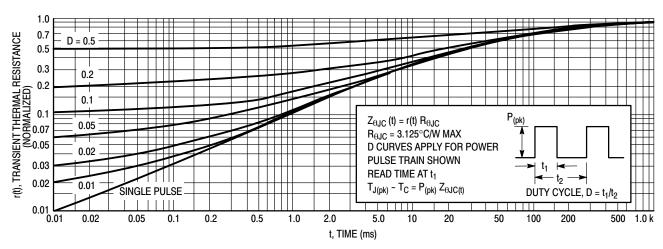


Figure 4. Thermal Response

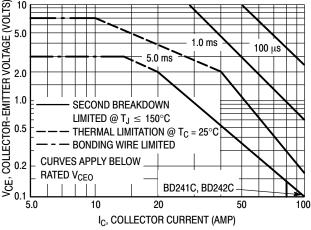


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150$ °C; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150$ °C, $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

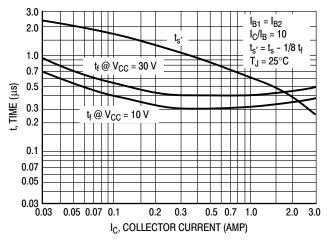


Figure 6. Turn-Off Time

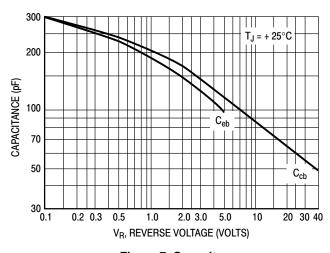


Figure 7. Capacitance

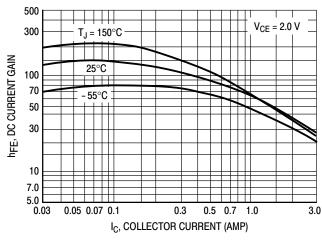


Figure 8. DC Current Gain

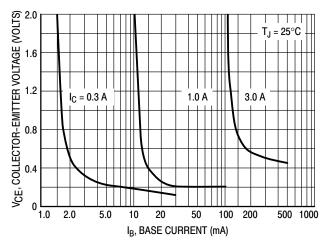


Figure 9. Collector Saturation Region

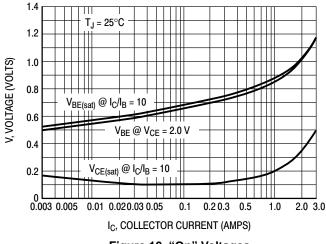


Figure 10. "On" Voltages

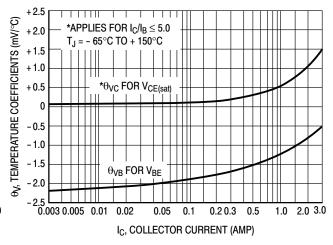
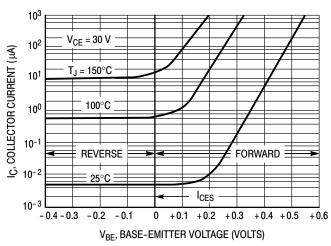


Figure 11. Temperature Coefficients





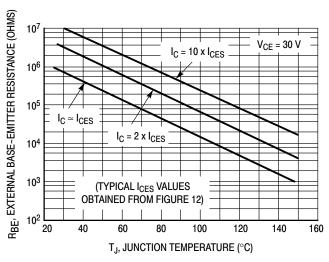
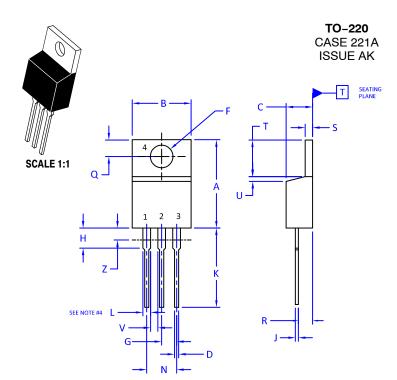


Figure 13. Effects of Base-Emitter Resistance





DATE 13 JAN 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	COLLECTOR	STYLE 3: PIN 1. 2. 3. 4.	ANODE	2. 3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	STYLE 6: PIN 1. 2. 3. 4.	CATHODE ANODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.			GATE SOURCE DRAIN SOURCE	STYLE 11: PIN 1. 2. 3. 4.		STYLE 12: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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